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09/9/6, 619

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L7 and tunneling	10

Database:

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[JPO Abstracts Database](#)
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Search:

L8

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DATE: Monday, July 28, 2003 [Printable Copy](#) [Create Case](#)
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Hit Count **Set Name**
 result set

DB=USPT; PLUR=YES; OP=ADJ

L8	L7 and tunneling	10	L8
L7	L6 and (floating adj gates)	10	L7
L6	L5 and (conductivity adj type)	10	L6
L5	L4 and array	19	L5
L4	L3 and Fowler	21	L4
L3	L2 and (memory adj device)	151	L3
L2	programmable and eraseable	383	L2
L1	programmable adj eraseable	7	L1

END OF SEARCH HISTORY

WEST[Generate Collection](#)[Print](#)**Search Results - Record(s) 1 through 10 of 10 returned.**☐ 1. Document ID: US 6252799 B1

L8: Entry 1 of 10

File: USPT

Jun 26, 2001

US-PAT-NO: 6252799

DOCUMENT-IDENTIFIER: US 6252799 B1

TITLE: Device with embedded flash and EEPROM memories

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC
Draw Desc	Image										

☐ 2. Document ID: US 6157575 A

L8: Entry 2 of 10

File: USPT

Dec 5, 2000

US-PAT-NO: 6157575

DOCUMENT-IDENTIFIER: US 6157575 A

TITLE: Nonvolatile memory device and operating method thereof

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC
Draw Desc	Image										

☐ 3. Document ID: US 5953255 A

L8: Entry 3 of 10

File: USPT

Sep 14, 1999

US-PAT-NO: 5953255

DOCUMENT-IDENTIFIER: US 5953255 A

** See image for Certificate of Correction **

TITLE: Low voltage, low current hot-hole injection erase and hot-electron programmable flash memory with enhanced endurance

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC
Draw Desc	Image										

☐ 4. Document ID: US 5293337 A

L8: Entry 4 of 10

File: USPT

Mar 8, 1994

US-PAT-NO: 5293337

DOCUMENT-IDENTIFIER: US 5293337 A

** See image for Certificate of Correction **

TITLE: Electrically erasable programmable read-only memory with electric field decreasing controller

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KMMC
Draw Desc	Image										

☐ 5. Document ID: US 5168335 A

L8: Entry 5 of 10

File: USPT

Dec 1, 1992

US-PAT-NO: 5168335

DOCUMENT-IDENTIFIER: US 5168335 A

TITLE: Electrically programmable, electrically erasable memory array cell with field plate

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KMMC
Draw Desc	Image										

☐ 6. Document ID: US 5100819 A

L8: Entry 6 of 10

File: USPT

Mar 31, 1992

US-PAT-NO: 5100819

DOCUMENT-IDENTIFIER: US 5100819 A

TITLE: Method of making electrically programmable and erasable memory cells with field plate conductor defined drain regions

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KMMC
Draw Desc	Image										

☐ 7. Document ID: US 5045489 A

L8: Entry 7 of 10

File: USPT

Sep 3, 1991

US-PAT-NO: 5045489

DOCUMENT-IDENTIFIER: US 5045489 A

TITLE: Method of making a high-speed 2-transistor cell for programmable/EEPROM devices with separate read and write transistors

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KVMC

☐ 8. Document ID: US 4951103 A

L8: Entry 8 of 10

File: USPT

Aug 21, 1990

US-PAT-NO: 4951103

DOCUMENT-IDENTIFIER: US 4951103 A

TITLE: Fast, trench isolated, planar flash EEPROMS with silicided bitlines

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KVMC

☐ 9. Document ID: US 4947222 A

L8: Entry 9 of 10

File: USPT

Aug 7, 1990

US-PAT-NO: 4947222

DOCUMENT-IDENTIFIER: US 4947222 A

TITLE: Electrically programmable and erasable memory cells with field plate conductor defined drain regions

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KVMC

☐ 10. Document ID: US 4701776 A

L8: Entry 10 of 10

File: USPT

Oct 20, 1987

US-PAT-NO: 4701776

DOCUMENT-IDENTIFIER: US 4701776 A

TITLE: MOS floating gate memory cell and process for fabricating same

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KVMC

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